

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

Claim 1 (canceled)

Claim 2 (canceled)

Claim 3 (original): A fabrication method, comprising the steps of:

- a) implanting first dopant atoms into a semiconductor body to create a first-conductivity-type well diffusion therein; and
- b) implanting second dopant atoms into said semiconductor body, with more than twice the stopping distance and less than one-quarter of the dosage per unit area as said step a), to compensate atoms which channeled during said step a).

Claim 4 (currently added): A method for forming devices on an integrated circuit, comprising:

- forming a shallow trench isolation structure in a semiconductor;
- forming a well in said semiconductor adjacent said shallow trench isolation structure by implanting dopant species of a first conductivity type into said semiconductor to a first depth;
- implanting dopant species of a second conductivity type into said well to a second depth wherein said second depth is greater than said first depth.

Claim 5 (currently added): The method of claim 4 wherein said forming said well further comprises simultaneously implanting, along with said dopant species of a first conductivity type to a first depth, dopant species of a first conductivity type to a second depth.

Claim 6 (currently added): The method of claim 5 wherein said implanting said dopant species of a second conductivity type comprises implanting boron ions in doses from  $1 \times 10^{11} \text{ cm}^{-2}$  to  $1 \times 10^{13} \text{ cm}^{-2}$  at energies from 500 keV to 900 keV.